IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

NAKAYAMA ET AL.

Atty. Ref.:

925-342

Serial No.

10/581,247

2811 Group:

Filed:

May 31, 2006

Examiner: Unknown

For:

SILICON CARBIDE SEMICONDUCTOR DEVICE AND

MANUFACTURING METHOD THEREFOR

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

## INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

☐ All listed documents are attached.

Copies of U.S. Patent Publications are not required and are not attached.

□ Listed foreign patent publications and other documents are enclosed.

The EP 1215730 reference corresponds to the WO 01/018872 reference; U.S.

Patent 6,121,633 corresponds to the JP 2002-514355 reference; and U.S. Patent 5,958,132 corresponds to the JP 7-267795 reference..

The listed documents were cited in the ISR and copies are submitted herewith for the Examiner's consideration in this US National Phase Application.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

NAKAYAMA ET AL. Serial No. 10/581,247

> The Commissioner is authorized to charge the undersigned's deposit account #14-1140 in whatever amount is necessary for entry of these papers and the continued pendency of the captioned application.

> > Respectfully submitted,
> > NIXON & VANDERHYE P.C.

By: Haller Seese

Reg. No. 29,366

January 8, 2007

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Examiner: Initial it	reference considered, whether or	not citation is in	conformance with MPEP 609	Draw line through cita	tion if not in confo	rmance and not	considered.	Include
copy of this form v	with next communication to applica	tion.				Form PTO-FB-		